

Rev. 0.2

64M Bits Serial Pseudo-SRAM with SPI and QPI

REVISION HISTORY

| Revision | <u>Description</u> | <u>Issue Date</u> |
|----------|--|-------------------|
| Rev. 0.1 | Initial Issued | May.19. 2016 |
| Rev. 0.2 | Revised the address bit length from 32 bits to 24 bits | Oct.13. 2016 |



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FEATURES

■ SPI compatible bus interface

-Clock rate:

33MHz(max) for normal read 100MHz(max) for fast read

-Mode: SPI/QPI

Low power consumption:

Operating current:

30mA(MAX./SPI@33MHz) 60mA(MAX./QPI@100MHz)

- Single 1.8V power supply
- Unlimited read/write cycle
- Fast write time as minimum cycle time
- 8M x 8-bit organization
 - -1K byte per page
- High Reliability
- Green package available
- Package: 8-pin 150 mil SOP

GENERAL DESCRIPTION

The LY68S6400 is a 64M-bit serial pseudo SRAM device organized as 8Mx8 bits. It is fabricated using very high performance, high reliability CMOS technology.

The LY68S6400 is accessed via a simple Serial Peripheral Interface(SPI) compatible serial bus. Additionally, Quad Peripheral Interface(QPI) is supported if your application needs faster data rates. This device also supports unlimited reads and writes to the memory array.

The LY68S6400 operates from a single power supply of 1.8V and can offer high data bandwidth at 100MHz clock rate and Serial Quad interface.

The LY68S6400 offers 8-lead SOP package.

PIN CONFIGURATION

| CE# | 1• | _ | 8 | Vcc |
|-----------|-----|---|---|-----------|
| SO/SIO[1] | 2 } | - - - - - - - - - - - - - - - - - - - | 7 | SIO[3] |
| SIO[2] | 3 🔀 | ntek S640 | 6 | SCLK |
| Vss | 4 | 0 | 5 | SI/SIO[0] |
| | ; | SOP | | |

PIN DESCRIPTION

| SYMBOL | SPI MODE | SQI MODE | |
|------------|--------------------|---------------|--|
| SI/SIOI[0] | Serial Input | Serial I/O[0] | |
| SO/SIO[1] | Serial Output | Serial I/O[1] | |
| SIO[2] | - | Serial I/O[2] | |
| SIO[3] | - | Serial I/O[3] | |
| CE# | Chip Select Input | t | |
| SCLK | Clock Signal Input | | |
| Vcc | Power Supply | | |
| Vss | Ground | | |

ABSOLUTE MAXIMUN RATINGS*

| PARAMETER | SYMBOL | RATING | UNIT |
|--|------------------|-----------------|----------------------|
| Voltage on V _{CC} relative to V _{SS} | V _{T1} | -0.5 to 2.3 | V |
| Voltage on any other pin relative to Vss | V _{T2} | -0.5 to Vcc+0.5 | V |
| Operating Temperature | T _A | -25 to 85 | $^{\circ}\mathbb{C}$ |
| Storage Temperature | T _{STG} | -65 to 150 | °C |

^{*}Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.



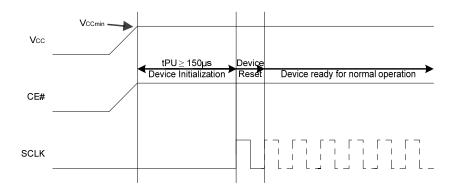
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POWER-UP INITIALIZATION

The LY68S6400 includes an on-chip voltage sensor used to start the self-initialization process. When $V_{\rm CC}$ reaches a stable level at or above minimum $V_{\rm CC}$, the device will require 150 μ s to complete its self-initialization process. From the beginning of power ramp to the end of the 150 μ s period, SCLK should remain LOW, CE# should remain HIGH(track $V_{\rm CC}$ within 200mV) and SI/SO/SIO[3:0] should remain LOW.

After the 150µs period, the device requires at least one clock during CE# high to properly reset the device, and then the device is ready for normal opearion.



Command/Address Latching Truth Table

| | | | SPI Mode | | | | | QPI Mod | е | | |
|----------------|------|-----|----------|---------------|-----|--------------|-----|---------|---------------|-----|--------------|
| Command | Code | Cmd | Addr | Wait Cycle | DIO | Max Freq. | Cmd | Addr | Wait Cycle | DIO | Max Freq. |
| Read | 03h | S | S | 0 | S | 33 | | | N/A | | |
| Fast Read | 0Bh | S | S | 8 | S | 100 | | | N/A | | |
| Quad Read | EBh | S | Q | 6 | Q | 100 | Q | Q | 6 | Q | 100 |
| Write | 02h | S | S | 0 | S | 100 | Q | Q | 0 | Q | 100 |
| Quad Write | 38h | S | Q | 0 | Q | 100 | Q | Q | 0 | Q | 100 |
| Enter QPI Mode | 35h | S | - | - | - | 100 | | | N/A | | |
| Exit QPI Mode | F5h | | | N/A | | | Q | - | - | - | 100 |

Note: S = Serial IO, Q = Quad IO

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DC ELECTRICAL CHARACTERISTICS

| PARAMETER | SYMBOL | TEST CON | DITION | MIN. | TYP. *1 | MAX. | UNIT |
|---------------------------------|------------------|---|------------|---------|----------------|---------|------|
| Supply Voltage | Vcc | | | 1.65 | 1.8 | 1.95 | V |
| Input High Voltage | ViH | | | Vcc-0.4 | - | Vcc+0.2 | V |
| Input Low Voltage | VIL | | | - 0.2 | - | 0.4 | V |
| Input Leakage Current | I⊔ | $V_{CC} \ge V_{IN} \ge V_{SS}$ | | - 1 | - | 1 | μA |
| Output Leakage Current | ILO | $V_{CC} \ge V_{OUT} \ge V_{SS}$, Output Disabled | | - 1 | - | 1 | μA |
| Output High Voltage | Vон | I _{OH} = -0.2mA | | 0.8*Vcc | - | - | V |
| Output Low Voltage | Vol | I_{OL} = +0.2mA | | - | - | 0.2*Vcc | V |
| Average Operating | lcc ₁ | CE# \leq 0.2, Others at 0.2V | SPI@33MHz | - | 6 | 15 | mA |
| Power Supply Current | ICC1 | or Vcc-0.2V I _{I/O} = 0mA;f=max | QPI@100MHz | - | 20 | 30 | mA |
| Standby Power Supply Current | I _{SB1} | CE# \geq V _{CC} - 0.2V, Others at 0.2V or V _C | cc - 0.2V | - | - | 200 | μΑ |

Notes:

^{1.} Typical values are included for reference only and are not guaranteed or tested. Typical valued are measured at V_{CC} = V_{CC} (TYP.) and T_A = 25°C



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CAPACITANCE $(T_A = 25^{\circ}C, f = 1.0 \text{MHz})$

| PARAMETER | SYMBOL | MIN. | MAX | UNIT |
|--------------------------|------------------|------|-----|------|
| Input Capacitance | Cin | - | 6 | pF |
| Input/Output Capacitance | C _{1/O} | - | 8 | pF |

Note: These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

| Input Pulse Levels | 0.2V to Vcc-0.2V |
|--|---|
| Input Rise and Fall Times | 1.5ns |
| Input and Output Timing Reference Levels | Vcc/2 |
| Output Load | $C_L = 30pF + 1TTL$, $I_{OH}/I_{OL} = -0.2mA/+0.2mA$ |

AC ELECTRICAL CHARACTERISTICS

| PARAMETER | SYM. | LY68 | S6400 | UNIT |
|-----------------------------------|------------------|------|-------|------------------|
| PARAMETER | STIVI. | MIN. | MAX. | UNII |
| Clock Cycle Time | tclk@33MHz | 30 | - | ns |
| Clock Cycle Time | tclk@100MHz | 10 | - | ns |
| Clock low width | t _{CL} | 0.45 | 0.55 | t _{CLK} |
| Clock high width | tсн | 0.45 | 0.55 | tclk |
| Clock rise time | t _R | - | 1.5 | ns |
| Clock fall time | t _F | - | 1.5 | ns |
| CE# setup time to CLK rising edge | t _{CSP} | 2.5 | - | ns |
| Setup time to active CLK edge | ts | 2.5 | - | ns |
| Hold time from active CLK edge | t _H | 2 | - | ns |
| Chip disable to DQ output high-Z | t _{HZ} | - | 7 | ns |
| CLK falling to output valid | taclk | - | 7 | ns |
| Output Hold from Clock falling | tон | 1.5 | - | ns |
| CE# low pulse width | tcem | - | 5 | us |

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SPI MODE OPERATIONS

The device powers up into SPI mode by default, but can also be switched into QPI mode.

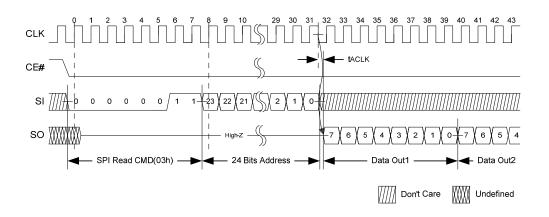
1. SPI Mode : Read Operations

For all reads, data will be available tACLK after the falling edge of CLK.

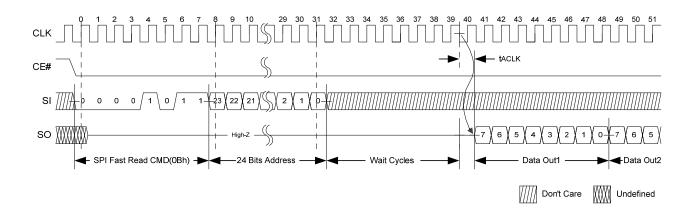
SPI Reads can be done in three ways:

- 1.1. 03h: Serial CMD, Serial IO, slow frequency
- 1.2. 0Bh: Serial CMD, Serial IO, fast frequency
- 1.3 EBh: Serial CMD, Quad IO, fast frequency

1.1 SPI Read(03h)



1.2 SPI Fast Read(0Bh)



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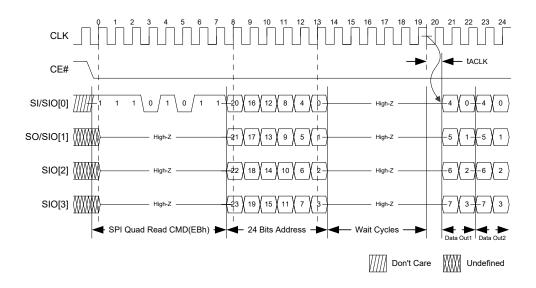




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1.3 SPI Quad Read(EBh)

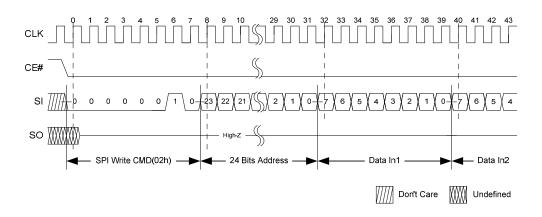


2. SPI Mode: Write Operations

SPI Writes can be done in two ways:

2.1 02h : Serial CMD, Serial IO, slow frequency 2.1 38h: Serial CMD, Quad IO, fast frequency

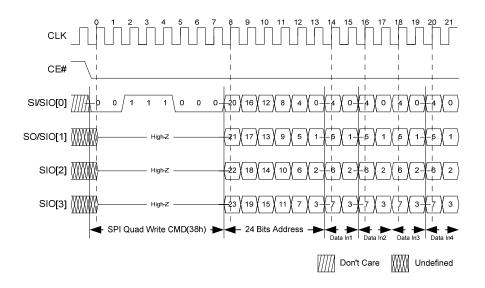
2.1 SPI Write(02h)





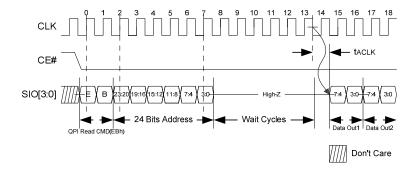
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2.2 SPI Quad Write(38h)

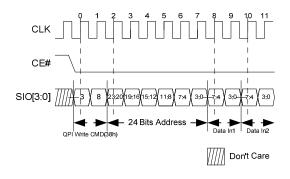


QPI MODE OPERATIONS

3. QPI Mode: Read Operations (EBh)



4. QPI Mode: Write Operations(38h or 02h)



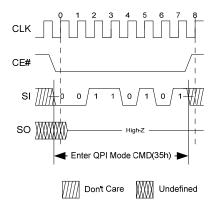




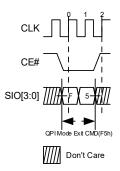
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5. QPI Mode: Enable Operation(35h)



6. QPI Mode: Quit Operation(F5h)



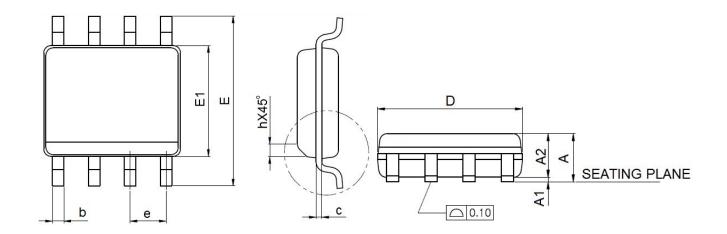


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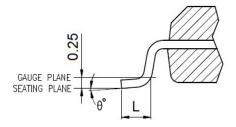
PACKAGE OUTLINE DIMENSION

8-pin 150mil SOP Package Outline Dimension



VARIATIONS (ALL DIMENSIONS SHOWN IN MM)

| SYMBOLS | STAN | DARD | | |
|----------|----------|------|--|--|
| 3 INDUL3 | MIN. | MAX. | | |
| Α | -8 | 1.75 | | |
| A1 | 0.10 | 0.25 | | |
| A2 | 1.25 | | | |
| Ь | 0.31 | 0.51 | | |
| С | 0.10 | 0.25 | | |
| D | 4.90 BSC | | | |
| Е | 6.00 | BSC | | |
| E1 | 3.90 BSC | | | |
| е | 1.27 | BSC | | |
| L | 0.40 | 1.27 | | |
| h | 0.25 | 0.50 | | |
| θ° | 0 | 8 | | |



NOTES:

1.JEDEC OUTLINE: MS-012 AA REV.F (STANDARD) MS-012 BA REV.F (THERMAL)

- 2.DIMENSIONS "D" DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.MOLD FLASH, PROTRUSIONS AND GATE BURRS SHALL NOT EXCEED 0.15mm. PER SIDE.
- 3.DIMENSIONS "E1" DOES NOT INCLUDE INTER-LEAD FLASH, OR PROTRUSIONS. INTER-LEAD FLASH AND PROTRUSIONS SHALL NOT EXCEED 0.25mm PER SIDE.



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ORDERING INFORMATION

| Package Type | Maximum Clock Rate(MHz) | Temperature Range(℃) | Packing Type | Lyontek Item No. |
|--------------|----------------------------|-------------------------|-----------------|------------------|
| 8-Pin | 100 | - 25℃~85℃ | Tube | LY68S6400SL |
| 150mil SOP | | 200 000 | Tape Reel | LY68S6400SLT |



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